

FDC636P

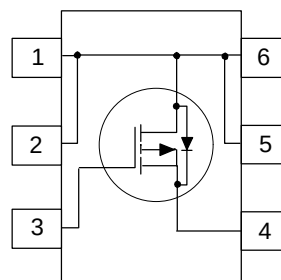
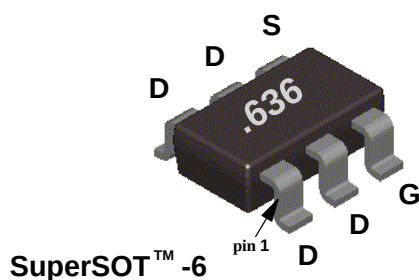
P-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These P-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching, and low in-line power loss are needed in a very small outline surface mount package.

Features

- -2.8 A, -20 V. $R_{DS(ON)} = 0.130 \Omega @ V_{GS} = -4.5 \text{ V}$
 $R_{DS(ON)} = 0.180 \Omega @ V_{GS} = -2.5 \text{ V}$.
- SuperSOT™-6 package design using copper lead frame for superior thermal and electrical capabilities.
- High density cell design for extremely low $R_{DS(ON)}$.
- Exceptional on-resistance and maximum DC current capability.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDC636P	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 8	V
I_D	Drain Current - Continuous (Note 1a)	-2.8	A
	- Pulsed	-11	
P_D	Maximum Power Dissipation (Note 1a)	1.6	W
	(Note 1b)	0.8	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	30	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _b = -250 μA	-20			V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temp. Coefficient	I _b = -250 μA, Referenced to 25 °C		-22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V			-1	μA
		T _j = 55°C			-10	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-0.6	-1	V
ΔV _{GS(th)} /ΔT _j	Gate Threshold VoltageTemp.Coefficient	I _D = -250 μA, Referenced to 25 °C		2		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = -4.5 V, I _D = -2.8 A		0.11	0.13	Ω
		T _j = 125°C		0.17	0.21	
		V _{GS} = -2.5 V, I _D = -2.2 A		0.146	0.18	
I _{D(on)}	On-State Drain Current	V _{GS} = -4.5 V, V _{DS} = -5 V	-11			A
g _{FS}	Forward Transconductance	V _{DS} = -5 V, I _D = -2.8 A		4		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V,		390		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		170		pF
C _{rss}	Reverse Transfer Capacitance			45		pF
SWITCHING CHARACTERISTICS (Note 2)						
t _{D(on)}	Turn - On Delay Time	V _{DD} = -10 V, I _D = -1 A,		30	48	ns
t _r	Turn - On Rise Time	V _{GS} = -4.5 V, R _{GEN} = 6 Ω		26	42	ns
t _{D(off)}	Turn - Off Delay Time			8	16	ns
t _f	Turn - Off Fall Time			15	27	ns
Q _g	Total Gate Charge	V _{DS} = -5 V, I _D = -2.8 A,		6	8.5	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -4.5 V		0.9		nC
Q _{gd}	Gate-Drain Charge			1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
I _S	Continuous Source Diode Current				-1.3	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -1.3 A (Note 2)		-0.77	-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
 - 78°C/W when mounted on a 1 in^2 pad of 2oz Cu on FR-4 board.
 - 156°C/W when mounted on a minimum pad of 2oz Cu on FR-4 board.
- Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Typical Electrical Characteristics

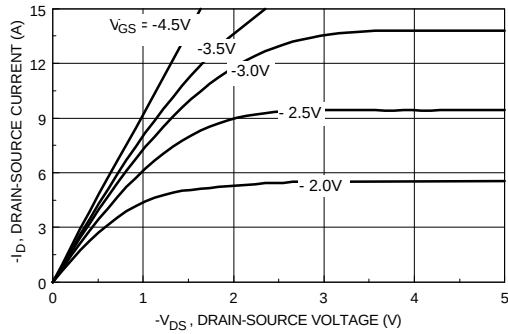


Figure 1. On-Region Characteristics.

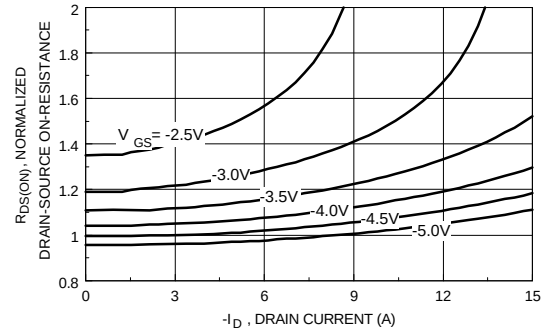


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

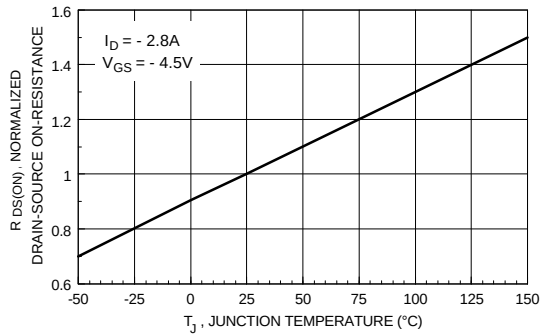


Figure 3. On-Resistance Variation with Temperature.

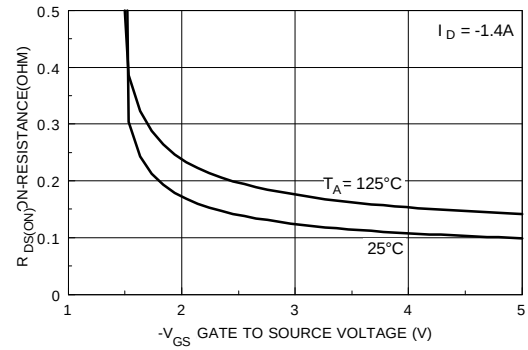


Figure 4. On-Resistance Variation with Gate-To-Source Voltage.

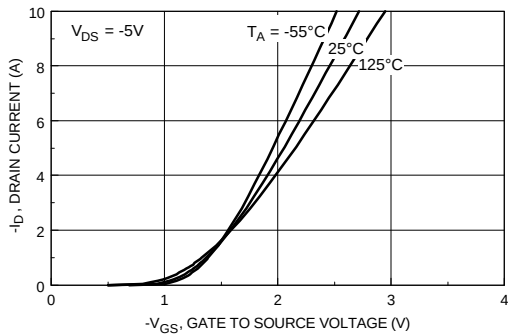


Figure 5. Transfer Characteristics.

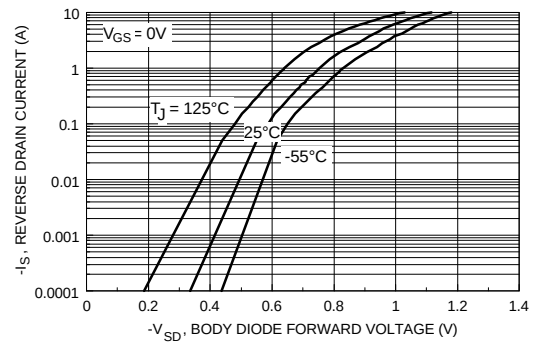


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics (continued)

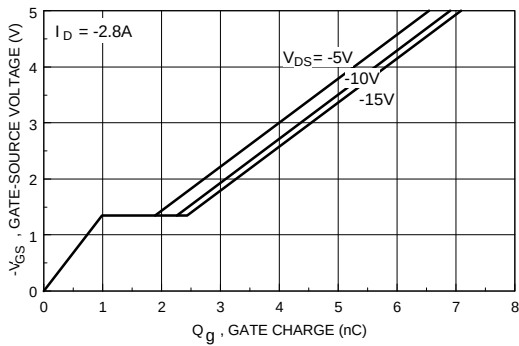


Figure 7. Gate Charge Characteristics.

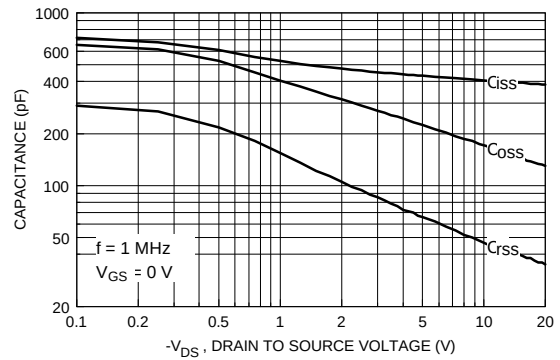


Figure 8. Capacitance Characteristics.

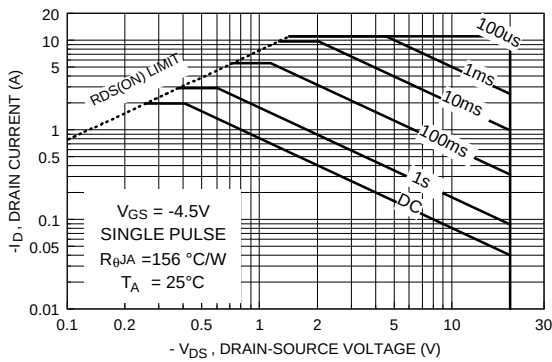


Figure 9. Maximum Safe Operating Area.

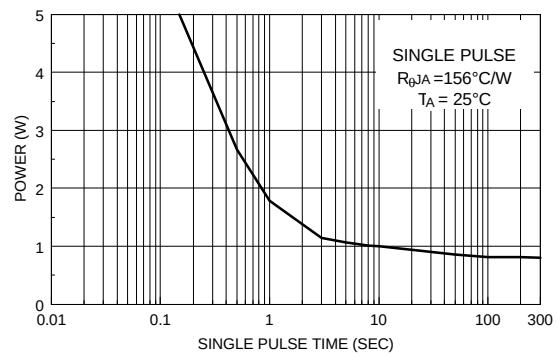


Figure 10. Single Pulse Maximum Power Dissipation.

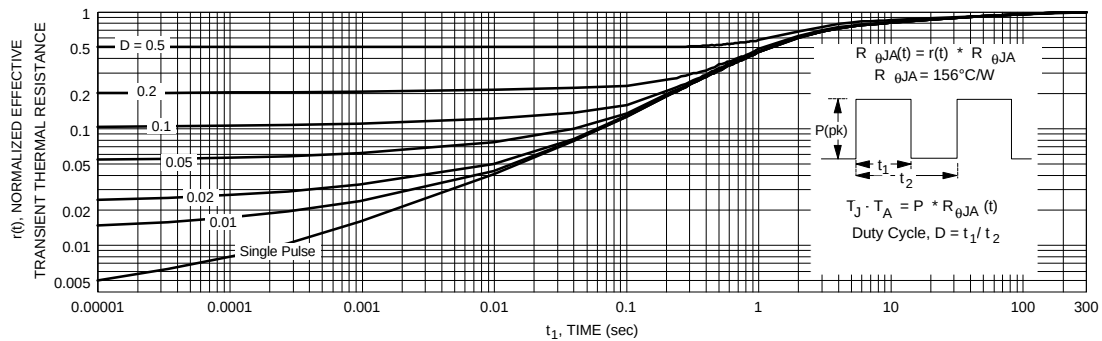


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1b.
Transient thermal response will change depending on the circuit board design.